

V_{DSS}	600V
$R_{DS(on)}(Max.)$	0.165Ω
I_D	±24A
P_D	74W

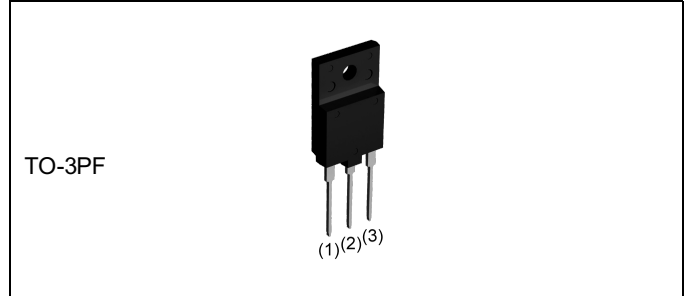
●Features

- 1) Low on-resistance.
- 2) Ultra fast switching speed.
- 3) Parallel use is easy.
- 4) Pb-free lead plating ; RoHS compliant

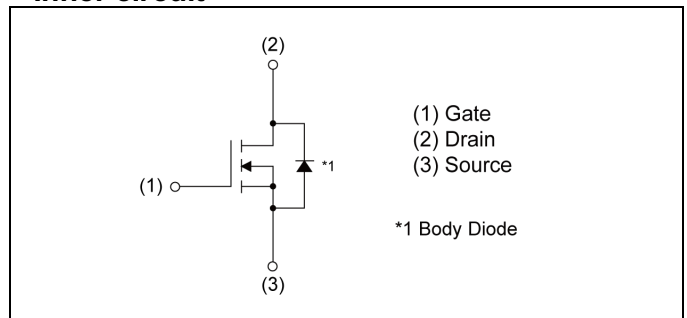
●Application

Switching

●Outline



●Inner circuit



●Packaging specifications

Type	Packing	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	360
	Taping code	C8
	Marking	R6024KNZ

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	600	V
Continuous drain current ($T_c = 25^\circ\text{C}$)	I_D^{*1}	±24	A
Pulsed drain current	I_{DP}^{*2}	±72	A
Gate - Source voltage	static	±20	V
	AC($f > 1\text{Hz}$)	±30	V
Avalanche current, single pulse	I_{AS}	4.1	A
Avalanche energy, single pulse	E_{AS}^{*3}	497	mJ
Power dissipation ($T_c = 25^\circ\text{C}$)	P_D	74	W
Junction temperature	T_j	150	°C
Operating junction and storage temperature range	T_{stg}	-55 to +150	°C

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}^{*4}	-	-	1.7	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	40	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	600	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$	-	-	100	μA
		$T_j = 125^\circ\text{C}$	-	-	1000	
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	3	-	5	V
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = 10V, I_D = 11.3A$	-	0.150	0.165	Ω
		$T_j = 125^\circ\text{C}$	-	0.32	-	
Gate resistance	R_G	$f = 1MHz, \text{open drain}$	-	1.9	-	Ω

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Forward Transfer Admittance	$ Y_{fs} ^{*5}$	V _{DS} = 10V, I _D = 12A	6.5	13.0	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	2000	-	pF
Output capacitance	C _{oss}	V _{DS} = 25V	-	1500	-	
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	60	-	
Turn - on delay time	t _{d(on)} ^{*5}	V _{DD} ≈ 300V, V _{GS} = 10V	-	30	-	ns
Rise time	t _r ^{*5}	I _D = 12A	-	50	-	
Turn - off delay time	t _{d(off)} ^{*5}	R _L ≈ 27.4Ω	-	60	-	
Fall time	t _f ^{*5}	R _G = 10Ω	-	12	-	

●Gate charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q _g ^{*5}	V _{DD} ≈ 300V	-	45	-	nC
Gate - Source charge	Q _{gs} ^{*5}	I _D = 24A	-	13	-	
Gate - Drain charge	Q _{gd} ^{*5}	V _{GS} = 10V	-	20	-	
Gate plateau voltage	V _(plateau)	V _{DD} ≈ 300V, I _D = 24A	-	6.8	-	V

*1 Limited only by maximum channel temperature allowed.

*2 Pw ≤ 10μs, Duty cycle ≤ 1%

*3 L ≐ 70mH, V_{DD}=50V, R_G=25Ω, STARTING T_j=25°C

*4 T_C=25°C

*5 Pulsed

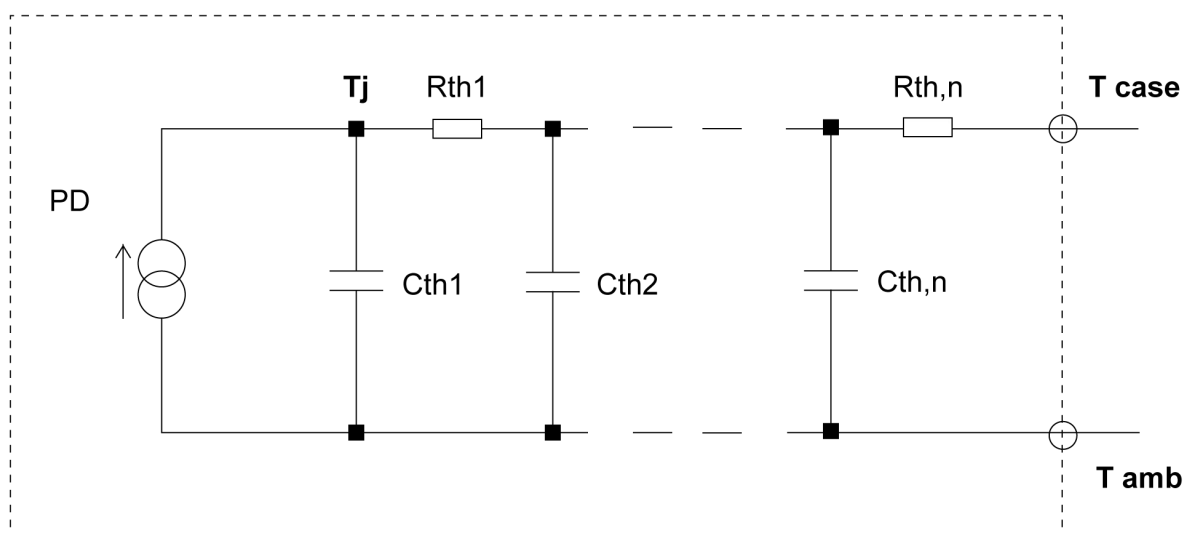
●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous forward current	I_S^{*1}	$T_C = 25^\circ\text{C}$	-	-	24	A
Pulse forward current	I_{SP}^{*2}		-	-	72	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0\text{V}, I_S = 24\text{A}$	-	-	1.5	V
Reverse recovery time	t_{rr}^{*5}	$I_S = 24\text{A}$ $di/dt = 100\text{A}/\mu\text{s}$	-	625	-	ns
Reverse recovery charge	Q_{rr}^{*5}		-	13.3	-	μC
Peak reverse recovery current	I_{rm}^{*5}		-	42	-	A

●Typical transient thermal characteristics

Symbol	Value	Unit
R_{th1}	0.108	K/W
R_{th2}	0.549	
R_{th3}	1.22	

Symbol	Value	Unit
C_{th1}	0.00523	Ws/K
C_{th2}	0.045	
C_{th3}	1.07	



● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

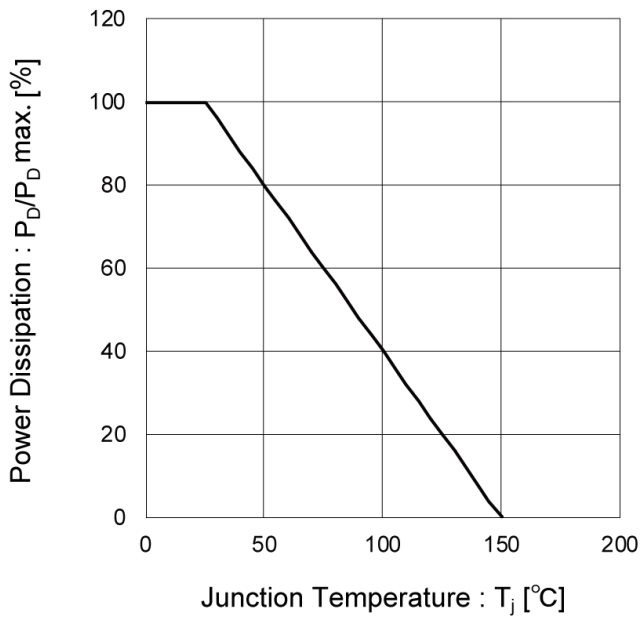


Fig.2 Maximum Safe Operating Area

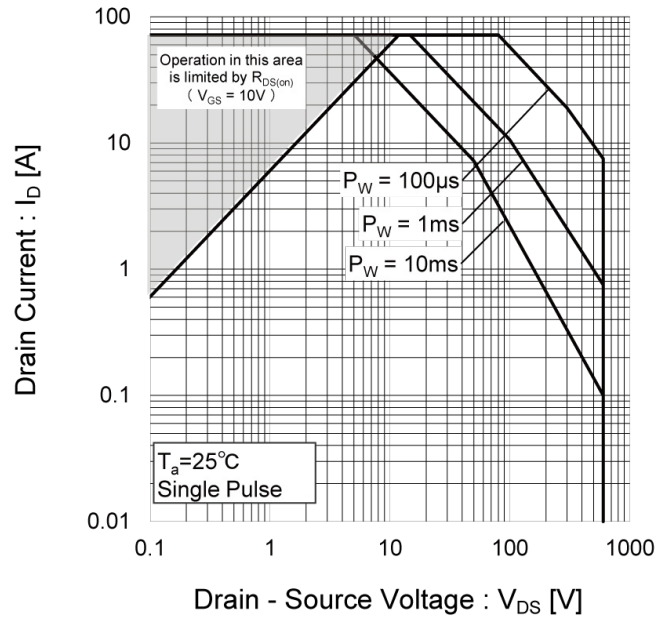
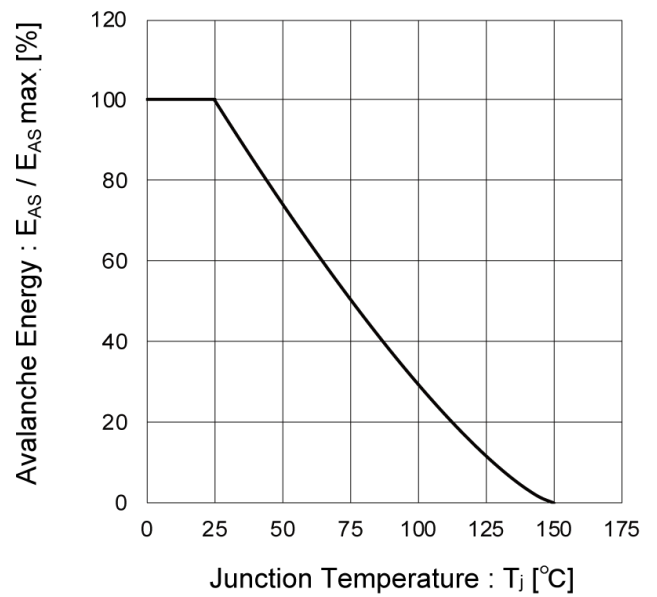


Fig.3 Avalanche Energy Derating Curve vs. Junction Temperature



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

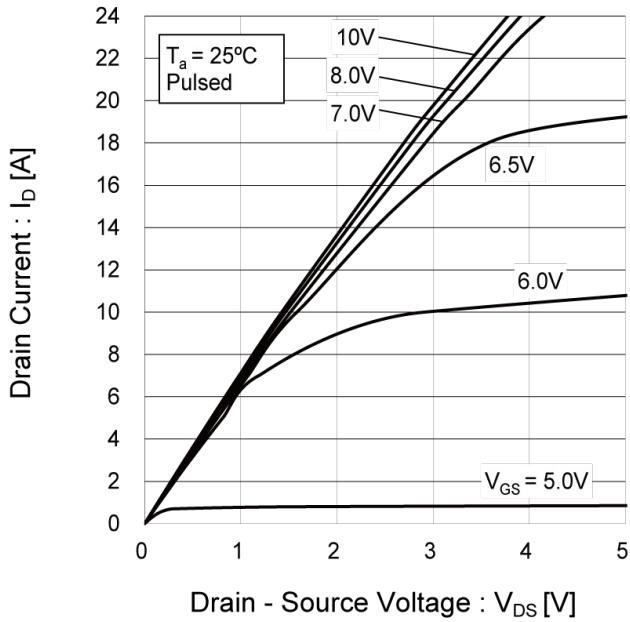
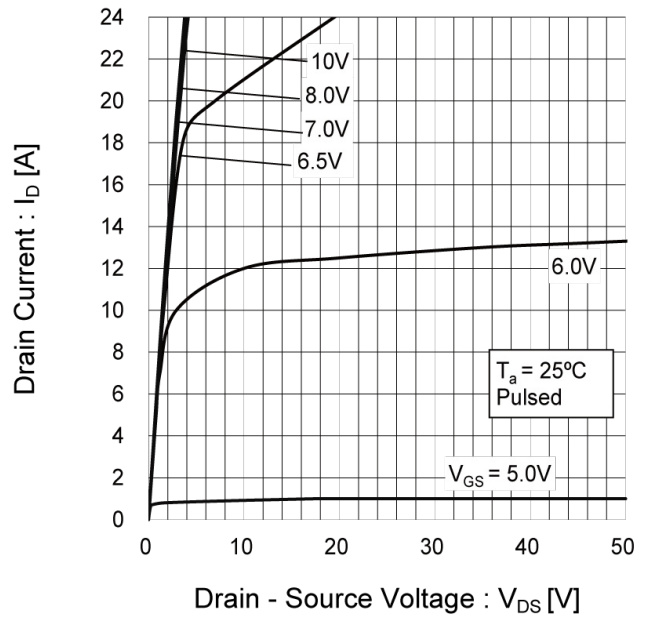


Fig.5 Typical Output Characteristics(II)



● Electrical characteristic curves

Fig.6 Breakdown Voltage vs. Junction Temperature

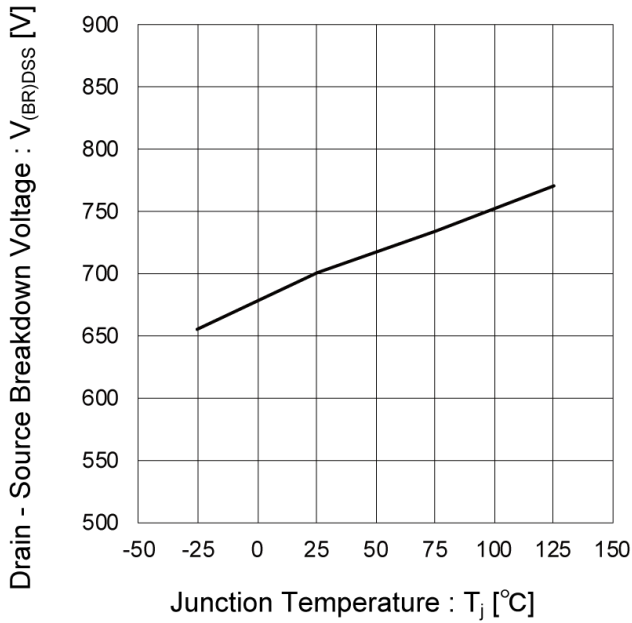


Fig.7 Typical Transfer Characteristics

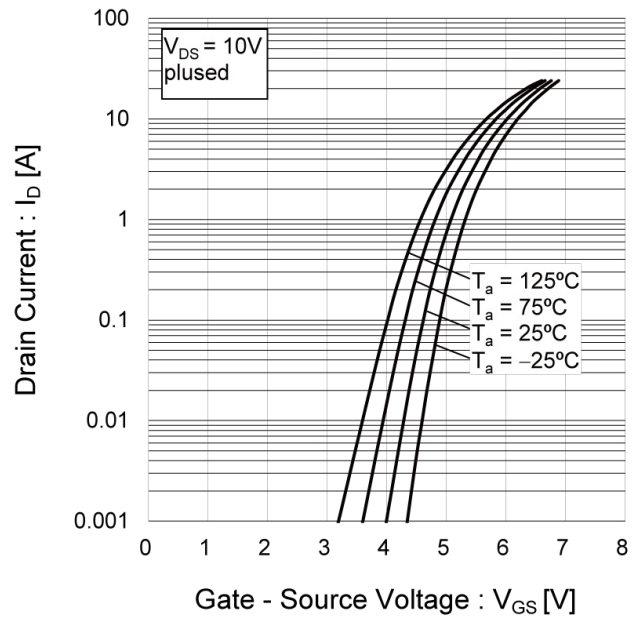


Fig.8 Gate Threshold Voltage vs. Junction Temperature

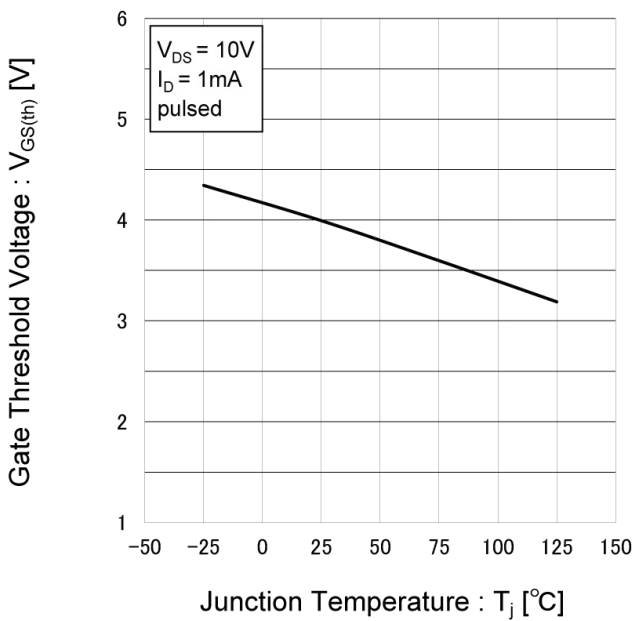
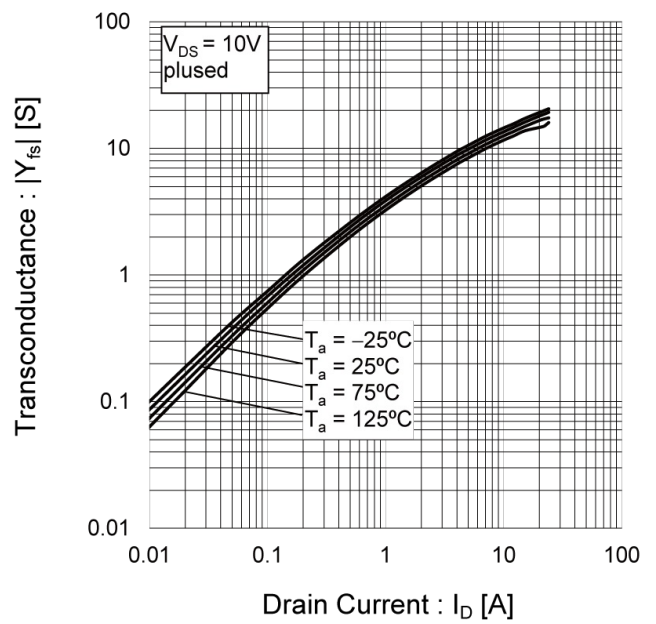


Fig.9 Forward Transfer Admittance vs. Drain Current



● Electrical characteristic curves

Fig.10 Static Drain - Source On - State Resistance vs. Gate Source Voltage

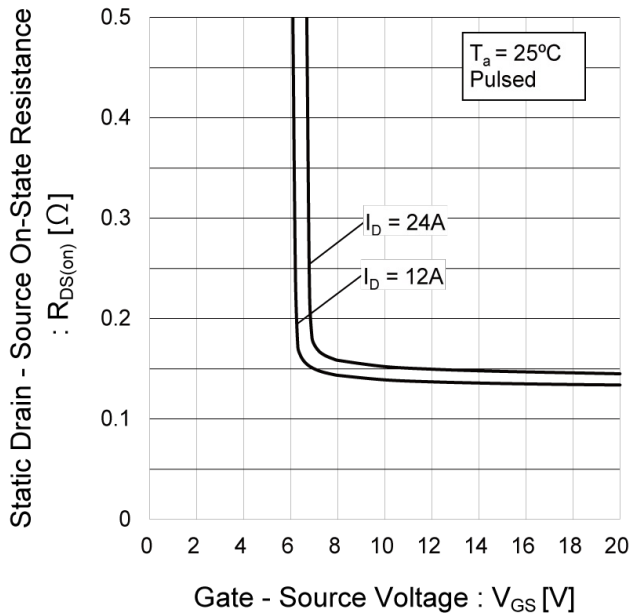


Fig.11 Static Drain - Source On - State Resistance vs. Junction Temperature

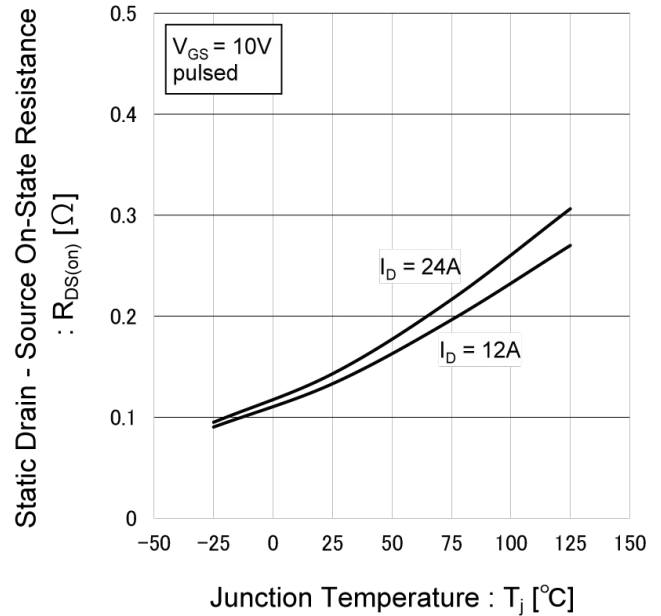
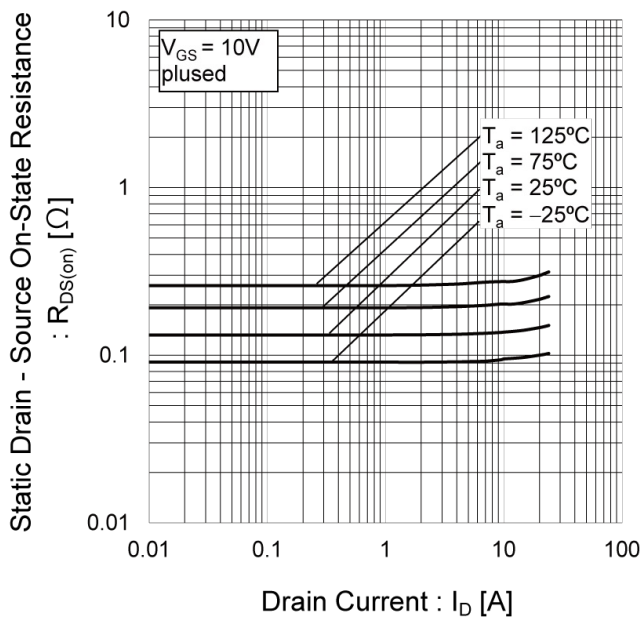


Fig.12 Static Drain - Source On - State Resistance vs. Drain Current(I)



● Electrical characteristic curves

Fig.13 Typical Capacitance vs. Drain - Source Voltage

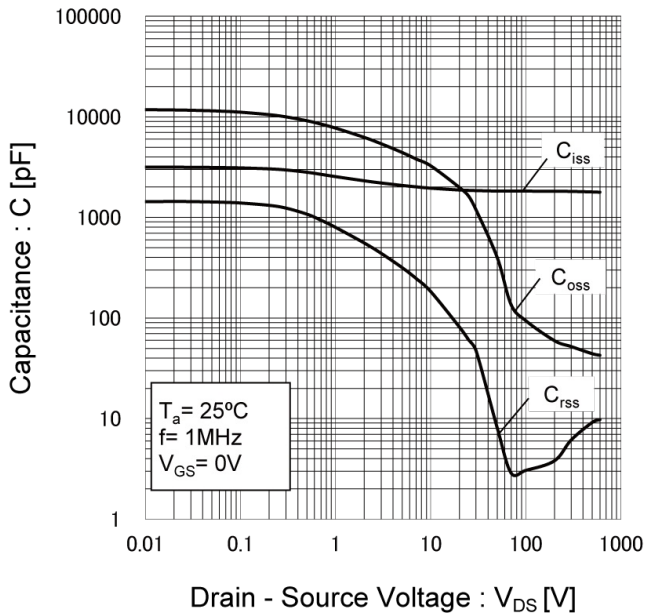


Fig.14 Switching Characteristics

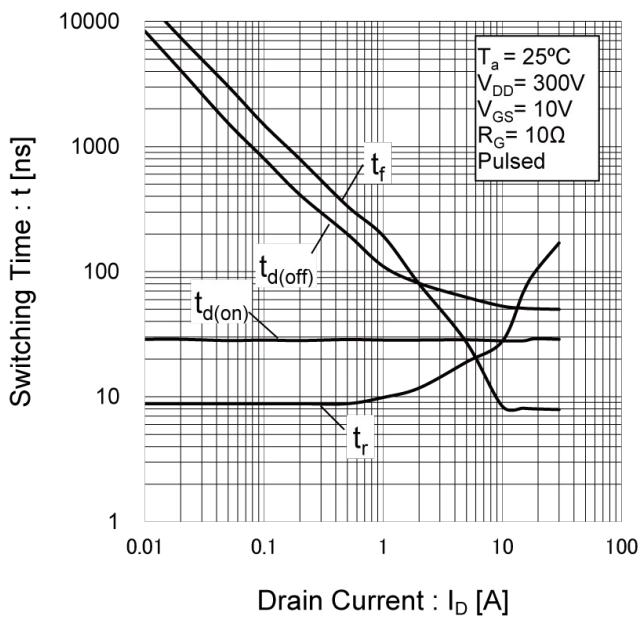
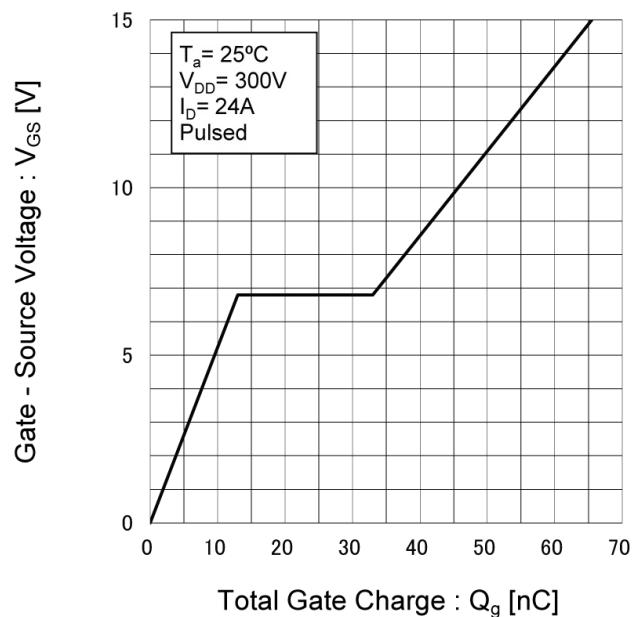


Fig.15 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.16 Inverse Diode Forward Current vs. Source - Drain Voltage

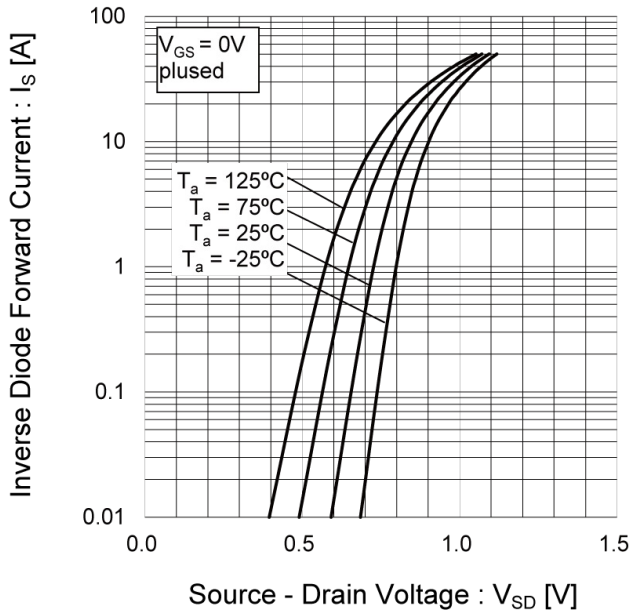
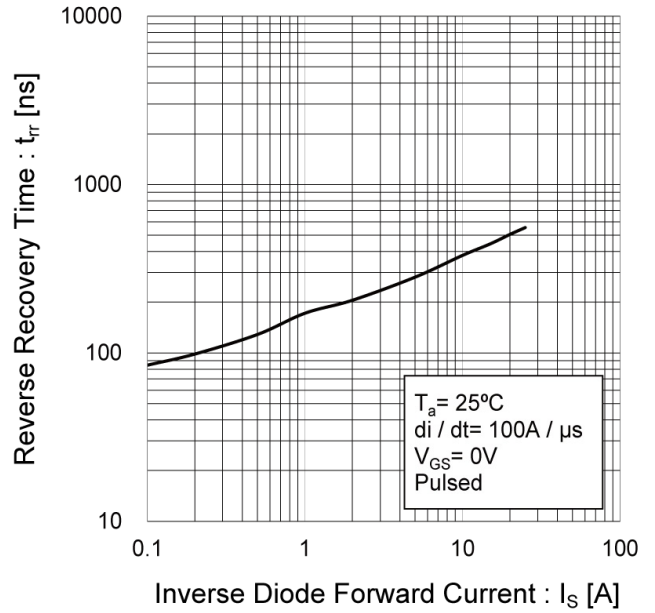


Fig.17 Reverse Recovery Time vs. Inverse Diode Forward Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit



Fig.1-2 Switching Waveforms



Fig.2-1 Gate Charge Measurement Circuit



Fig.2-2 Gate Charge Waveform



Fig.3-1 Avalanche Measurement Circuit



Fig.3-2 Avalanche Waveform



Fig.4-1 dv/dt Measurement Circuit

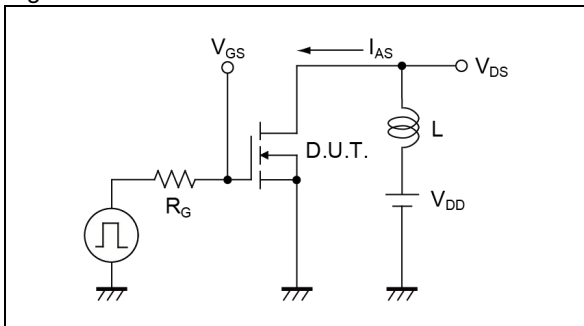


Fig.4-2 dv/dt Waveform

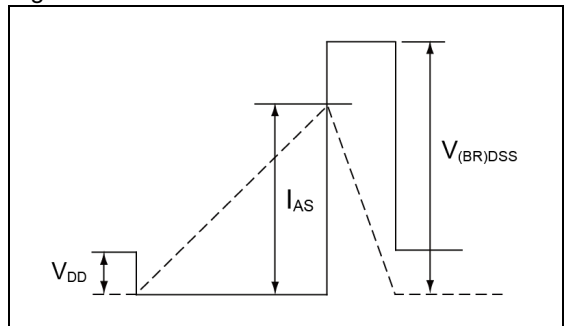


Fig.5-1 dv/dt Measurement Circuit

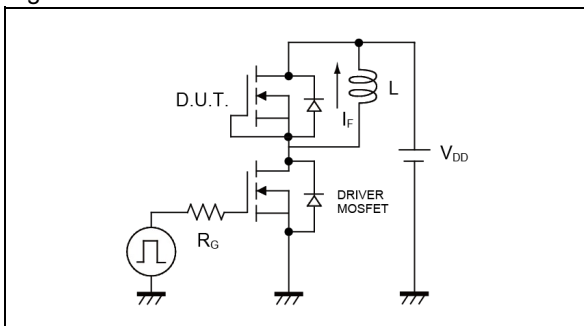
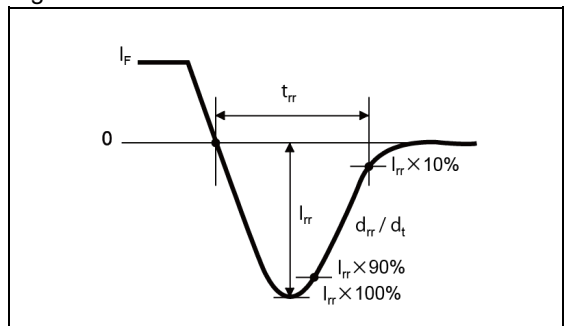
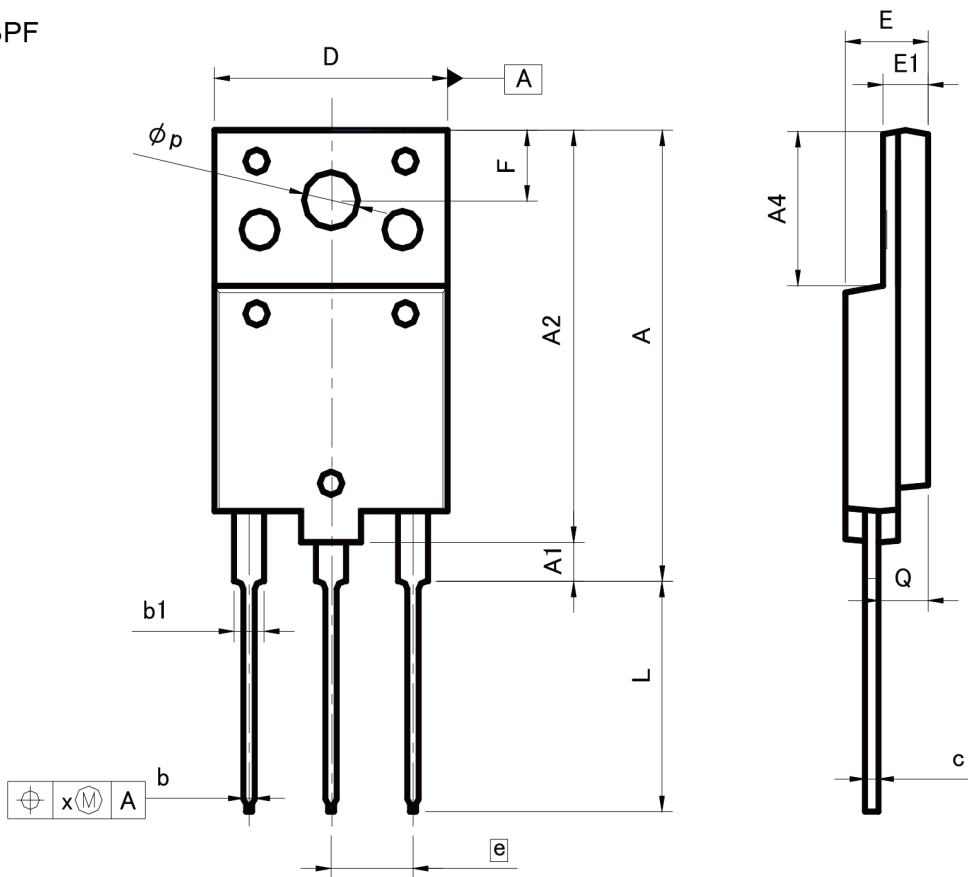


Fig.5-2 dv/dt Waveform



●Dimensions

TO-3PF



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	26.30	26.70	1.035	1.051
A1	2.30	2.70	0.091	0.106
A2	26.30	26.70	1.035	1.051
A4	9.80	10.20	0.386	0.402
b	0.65	0.95	0.026	0.037
b1	1.80	2.20	0.071	0.087
c	0.80	1.10	0.031	0.043
D	15.30	15.70	0.602	0.618
E	5.30	5.70	0.209	0.224
e	5.45		0.215	-
E1	2.80	3.20	0.110	0.126
F	4.30	4.70	0.169	0.185
L	14.60	15.00	0.575	0.591
p	3.40	3.80	0.134	0.150
Q	3.10	3.50	0.122	0.138
x	-	0.50	-	0.020

Dimension in mm/inches

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